

SILICON HYPERABRUPT VARACTOR DIODE

DESCRIPTION:

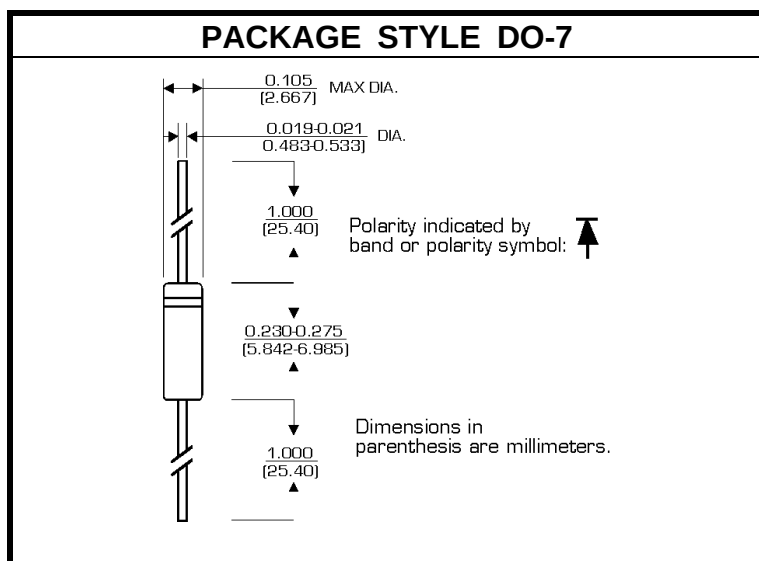
The **ASI DKV6510-12** is an Ion Implanted Silicon Hyperabrupt Varactor Diode Designed for Octave Tuning up to 500 MHz.

FEATURES INCLUDE:

- Large Tuning Ratio – **14:1** Typ.
- High **Q** – **700** Typ.
- Hermetic Glass **DO-7** Package

MAXIMUM RATINGS

I_F	100 mA
V_R	12 V
P_{DISS}	400 mW @ T _C = 25 °C
T_J	-55 °C to +150 °C
T_{STG}	-65 °C to +200 °C



CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
V_{BR}	I _R = 10 μA		12			V
I_R	V _R = 10 V				100	mA
C_{T2}	V _R = 2.0 V	f = 1.0 MHz	45		75	pF
C_{T10}	V _R = 10 V	f = 1.0 MHz	4.0		7.0	pF
C_{T2}/ C_{T10}	V _R = 2 & 10 V	f = 1.0 MHz	10.0		17.0	---
Q	V _R = 2.0 V	f = 1.0 MHz	200	700		---